















**ESD** 

TVS

MOS

LDO

Diode

Sensor

DC-DC

# **Product Specification**

Domestic Part Number	EV2SC5198-T72
Overseas Part Number	2SC5198
▶ Equivalent Part Number	2SC5198

"T72" means TO-3PS

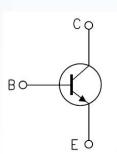




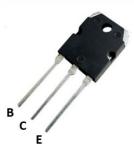
#### Silicon NPN transistor

#### **Power Amplifier Applications**

- Complementary to 2SA1941
- High collector voltage:VCEO=140V (min)
- Recommended for 100-W high-fidelity audio frequency amplifier Output stage



Note1: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



TO-3PS

## Absolute Maximum Ratings(Tc=25 $^{\circ}$ C):

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	140	V
Collector-emitter voltage	Vceo	140	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	Ic	10	А
Bese current	I <sub>B</sub>	1	А
Collector power dissipation(Tc=25°C)	Pc	100	W
Junction temperature	Tj	150	$^{\circ}$
Storage temperature range	Тѕтб	-55~150	$^{\circ}$



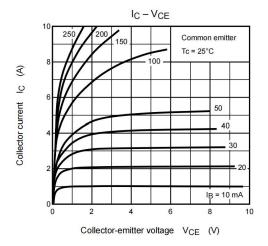
#### Silicon NPN transistor

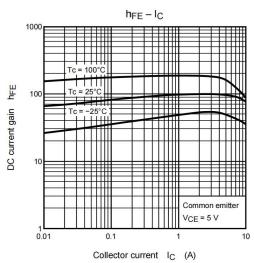
### Electrical Characteristics (Tc=25 $^{\circ}$ C):

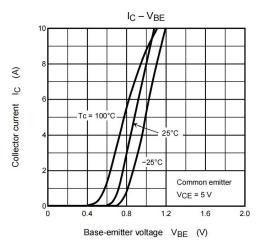
Characteristics	Symbol	Test Condition	Min	Тур	Max	Unit
Collector cut-off current	Ісво	V <sub>CB</sub> =140V; I <sub>E</sub> =0			5	uA
Emitter cut-off current	Гево	V <sub>EB</sub> =5V; I <sub>c</sub> =0			5	uA
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =50mA,I <sub>B</sub> =0	140			V
Dc current gain	hfe	Vce=5V; Ic=1A;	55		160	
	h <sub>FE(2)</sub>	Vce=5V; Ic=5A;	35	83		
Collector-emitter saturation voltage	Vce(sat)	Ic=8A; IB=0.8A			3.0	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =5V;I <sub>C</sub> =5A			1.5	
Transition frequency	f⊤	VCE=5V; IC=1A		30		MHz

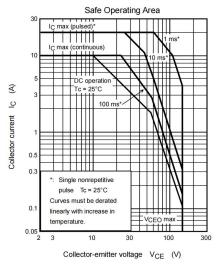
Symbol	Paramter	Тур	Units
$R_{ heta JC}$	Junction-to-Case	0.35	°C/W

#### **TYPICAL CHARACTERISTICS**







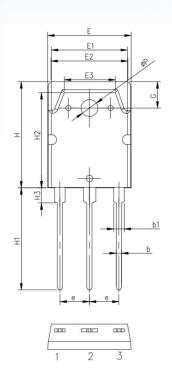


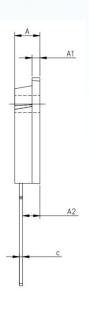


## **Package Information**

#### Silicon NPN transistor

#### TO-3PS PACKAGE





Symbol	单位 mm			
Symbol	Min	Nom	Max	
А	4.30	4.50	4.70	
A1	1.3	1.5	1.7	
A2	2.50	2.70	2.90	
b	0.80	1.0	1.20	
b1	1.80	2.00	2.20	
С	0.50	0.60	0.70	
е	5.25	5.45	5.65	
E	15.1	15.5	15.9	
E1	13.1	13.3	13.5	
E2	13.2	13.4	13.6	
E3	9.1	9.3	9.5	
Н	19.8	20.0	20.2	
H1	20.0	20.5	21.0	
H2	18.3	18.5	18.7	
Н3	2.8	3.0	3.2	
G	4.30	4.50	4.70	
ФР	3.00	3.20	3.40	



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